

# **Device Modeling Report**

**COMPONENTS:**

DIODE/ GENERAL PURPOSE RECTIFIER/ STANDARD

PART NUMBER: 1S1887A

MANUFACTURER: TOSHIBA

REMARK: TC=25C

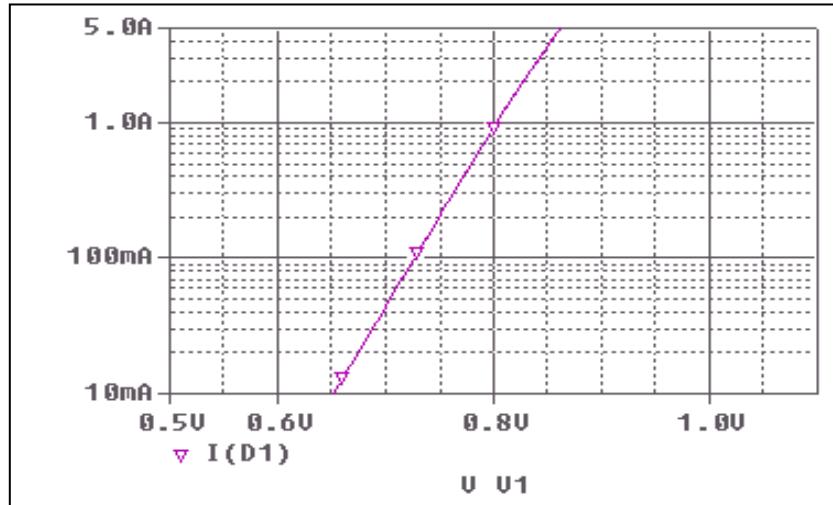


**Bee Technologies Inc.**

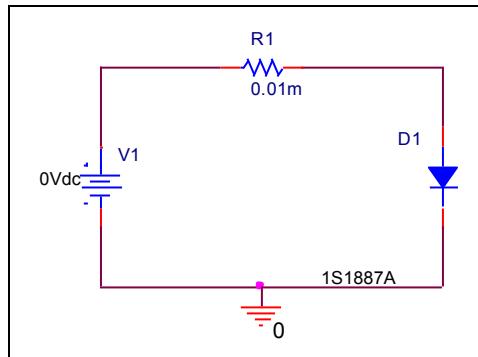
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

## Forward Current Characteristic

Circuit Simulation Result

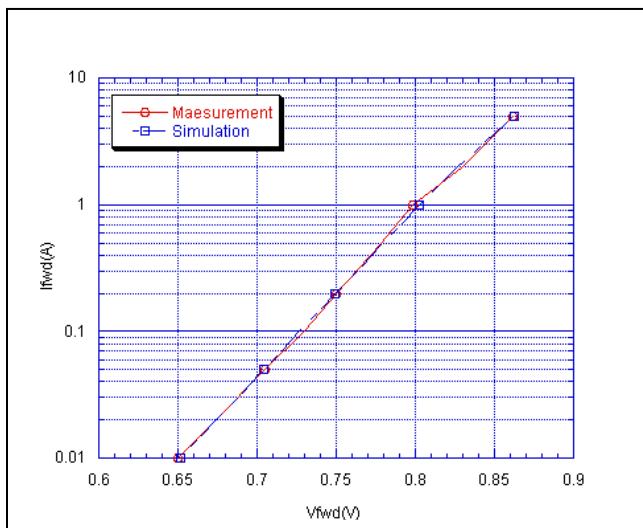


Evaluation Circuit



## Comparison Graph

### Circuit Simulation Result

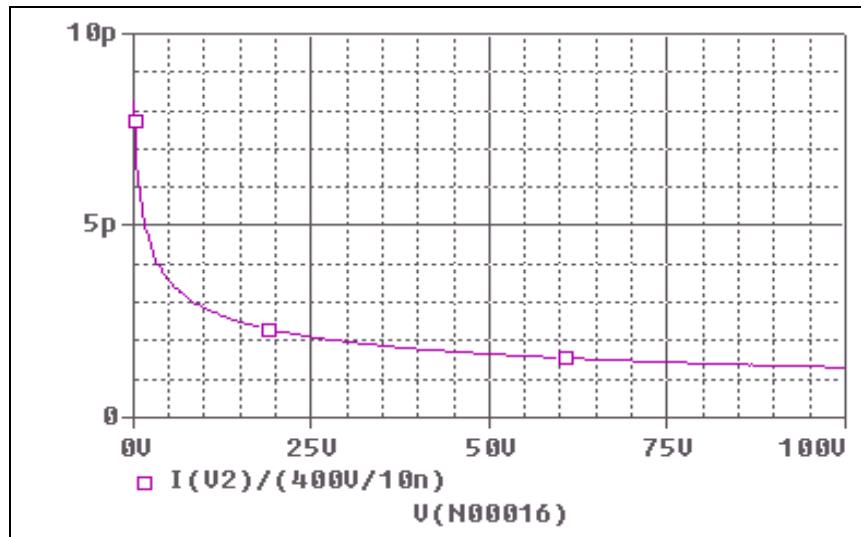


### Simulation Result

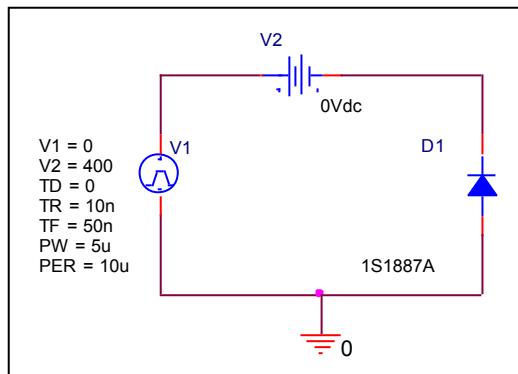
Ifwd(A)	Vfwd(V) Measurement	Vfwd(V) Simulation	%Error
0.01	0.650	0.652	-0.277
0.02	0.674	0.674	-0.045
0.05	0.705	0.704	0.156
0.1	0.730	0.727	0.438
0.2	0.750	0.749	0.133
0.5	0.778	0.779	-0.154
1	0.798	0.803	-0.576
2	0.830	0.827	0.373
5	0.862	0.861	0.116

## Junction Capacitance Characteristic

### Circuit Simulation Result

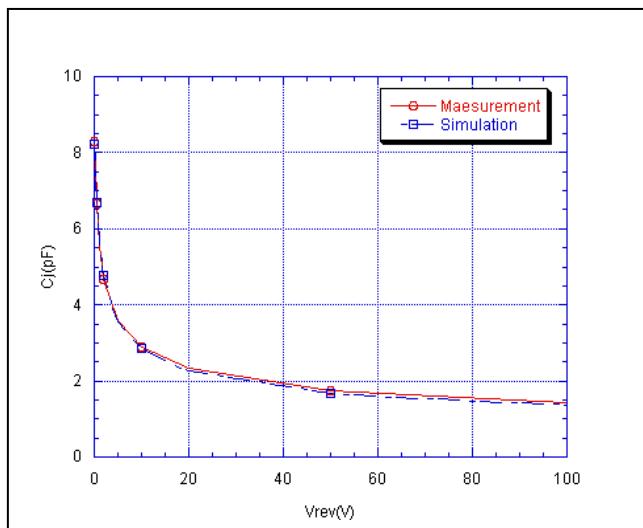


### Evaluation Circuit



## Comparison Graph

### Circuit Simulation Result

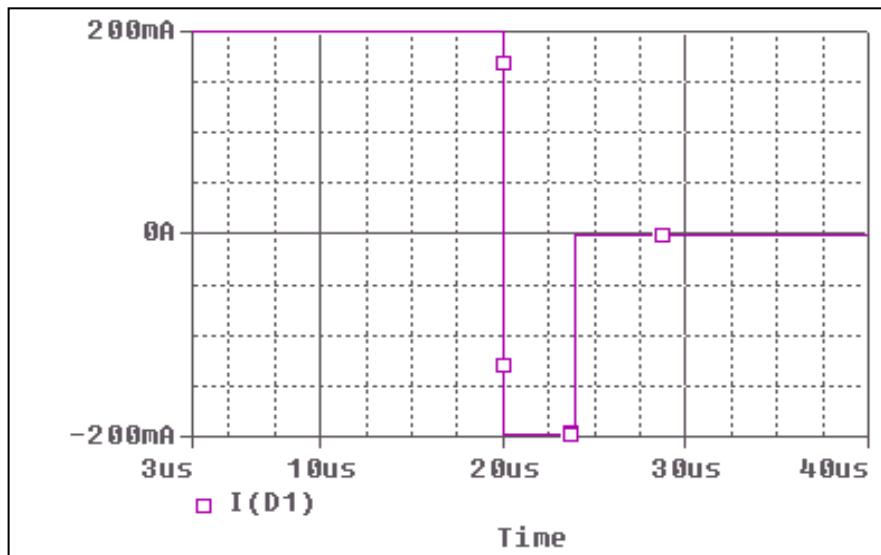


### Simulation Result

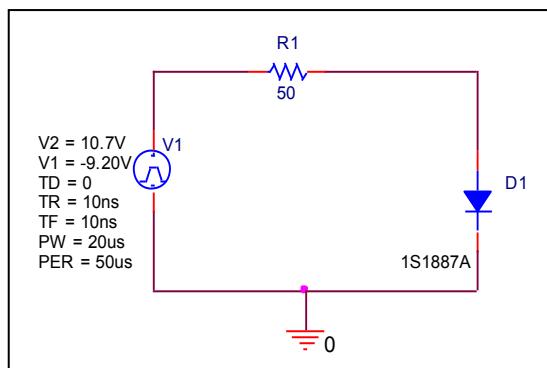
Vrev(V)	Cj(pF) Measurement	Cj(pF) Simulation	%Error
0	8.925	8.925	0.000
0.1	8.312	8.240	0.858
0.2	7.783	7.728	0.704
0.5	6.660	6.684	-0.354
1	5.568	5.732	-2.945
2	4.681	4.777	-2.040
5	3.584	3.571	0.352
10	2.895	2.860	1.206
20	2.323	2.272	2.179
50	1.734	1.690	2.498
100	1.387	1.338	3.518

## Reverse Recovery Characteristic

### Circuit Simulation Result



### Evaluation Circuit

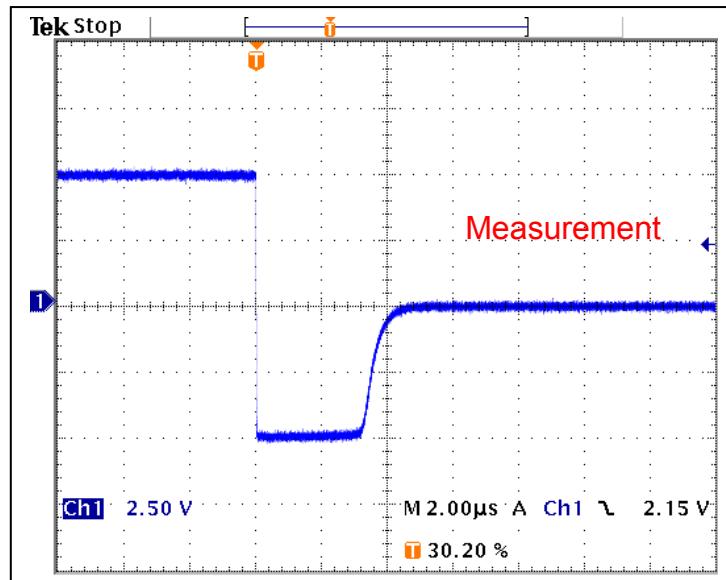


### Compare Measurement vs. Simulation

	Measurement		Simulation		%Error
trr	4.000	us	3.92	us	1.825

## Reverse Recovery Characteristic

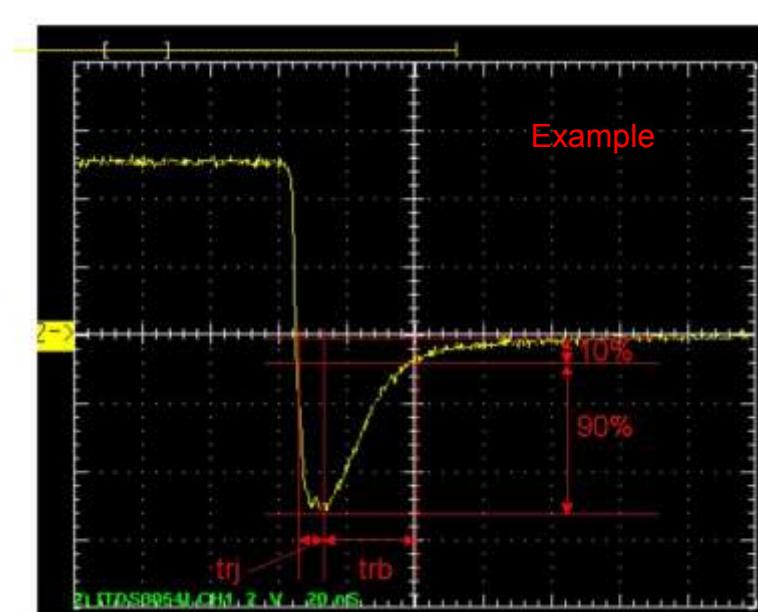
Reference



$Trj = 3.12(\mu s)$

$Trb = 0.88(\mu s)$

Conditions:  $I_{fwd} = I_{rev} = 0.2(A)$ ,  $R_I = 50$



Relation between  $trj$  and  $trb$